

**Amendments to the Specification:**

Please replace the paragraph beginning at page 5, line 1 with the following amended paragraph:

FIG. 19 is a I-V ~~plot of~~ plot of the silicon cones shown in FIG. 17 (b),

Please replace the paragraph beginning at page 6, line 7 with the following amended paragraph:

The fabrication of cone arrays is carried out by argon ion sputtering, while the argon ions are generated ~~from~~ from the ion source. The argon gas pressure is controlled at  $2 \times 10^{-4}$  Torr. Argon is one possible sputtering gas that may be used with the present invention, other gases such as helium, neon, xenon, or hydrogen etc. are equally possible. The ion energy used in the present invention ranges from 100 eV to 1000 eV. The incident angle of the ion-beam varies from 0 to 90 degree, the substrate temperature varies from 100C to 600C, and the fabrication time varies from 30 minutes to 4 hours for each individual process.